



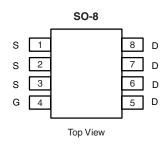
N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
	0.0045 at V _{GS} = 10 V	22		
30	0.005 at V _{GS} = 4.5 V	19		
	0.0075 at V _{GS} = 2.5 V	17		

FEATURES

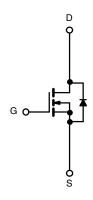
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFETs: 2.5 V Rated
- 100 % R_g Tested





Ordering Information: Si4442DY-T1-E3 (Lead (Pb)-free)

Si4442DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T	_A = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	30		V
Gate-Source Voltage		V _{GS}	± 12		
Continuous Dunis Comment /T 150 90\8	T _A = 25 °C	- I _D	22	15	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		17	11	
Pulsed Drain Current (10 µs Pulse Width)		I _{DM}	60		Α
Continuous Source Current (Diode Conduction) ^a		I _S	2.9	1.3	
	T _A = 25 °C	D.	3.5	1.6	W
Maximum Power Dissipation ^a	T _A = 70 °C	- P _D	2.2	1	VV
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Mariana basis to Auditoria	t ≤ 10 s	D	29	35	
Maximum Junction-to-Ambient ^a	Steady State	R _{thJA}	67	80	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	13	16	

Notes

a. Surface Mounted on 1" x 1" FR4 board.

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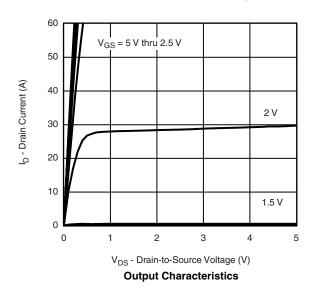
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static			1	<u>'</u>	<u> </u>		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$			1.5	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$	V _{DS} = 0 V, V _{GS} = ± 12 V		± 100	nA	
Zava Cata Valtaga Drain Current	1	V _{DS} = 30 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			5	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α	
		V _{GS} = 10 V, I _D = 22 A	0.0035 0.0045		0.0045		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 19 \text{ A}$		0.0041	0.005	Ω	
		$V_{GS} = 2.5 \text{ V}, I_D = 17 \text{ A}$		0.0062	0.0075		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 22 A		100		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 2.9 A, V _{GS} = 0 V		0.75	1.1	V	
Dynamic ^b							
Total Gate Charge	Q_g			36	50		
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 22 \text{ A}$		8		nC	
Gate-Drain Charge	Q_{gd}			10.5			
Gate Resistance	R_{g}		0.5	1.5	2.6	Ω	
Turn-On Delay Time	t _{d(on)}			17	30		
Rise Time	t _r	V_{DD} = 15 V, R_L = 15 Ω		11	20		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 1 A, V_{GEN} = 10 V, R_g = 6 Ω		125	180	ns	
Fall Time	t _f			47	70		
Source-Drain Reverse Recovery Time	e-Drain Reverse Recovery Time t_{rr} $I_F = 2.9 \text{ A}, \text{ dI/dt} = 100 \text{ A/µs}$			50	80		

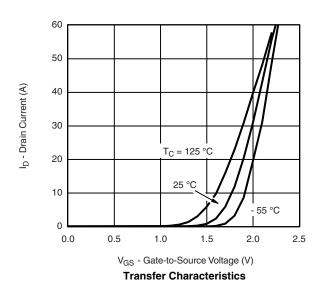
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



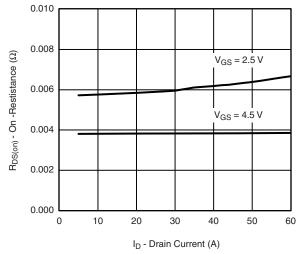




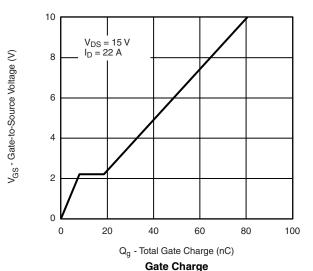


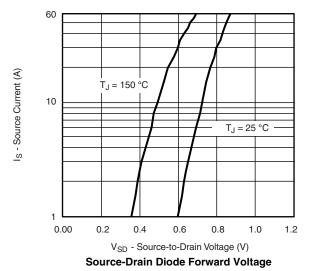


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



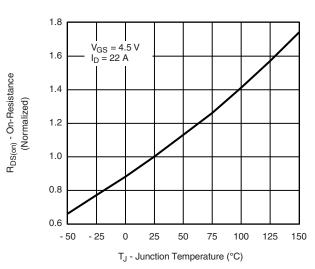
On-Resistance vs. Drain Current



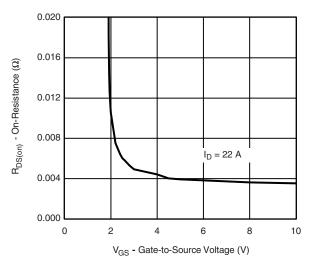


6000 5000 C_{iss} C - Capacitance (pF) 4000 3000 2000 Coss 1000 C_{rss} 0 0 12 18 24 30 V_{DS} - Drain-to-Source Voltage (V)

Capacitance



On-Resistance vs. Junction Temperature

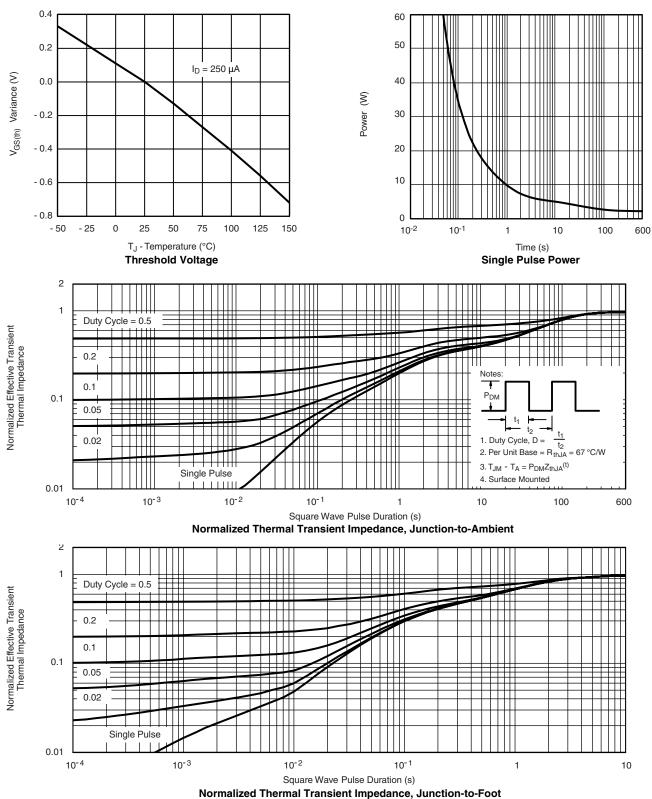


On-Resistance vs. Gate-to-Source Voltage

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INC	INCHES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
FCN: C-06527-Bey 11-Sen-06						

DWG: 5498

Document Number: 71192 www.vishay.com 11-Sep-06



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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Revision: 02-Oct-12 Document Number: 91000

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